NSN 5962-01-395-6316

Memory Microcircuit - Page 1 of 2

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Maximum Power Dissipation Rating:

1.2 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Pacer dawn

Features Provided:

Burn in, mil-std-883, class b and bipolar and electrostatic sensitive and hermetically sealed and monolithic and programmed and tested to mil-std-883

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

20 input

Criticality Code Justification:

Feat

Current Rating Per Characteristic:

100.00 milliamperes reverse current, dc and 1.00 milliamperes reverse current, dc microamperes and 210.00 milliamperes reverse current, dc absolute

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, digital, pal, wait state generator

Voltage Rating And Type Per Characteristic:

-1.5 volts input and 5.5 volts input and -0.5 volts power source and 7.0 volts power source

Time Rating Per Chacteristic:

20.00 nanoseconds input to output access

Memory Device Type:

Pal

Special Features:

Esd; altered item programmed from 67268 5962-8767101lx using pg639000-01 program; case size is gdip3-t24 or cdip4-t24

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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